

### **In the Claims**

Claims 1-34 (cancelled).

Claim 35 (previously presented): Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

an inner conductive core spaced from and suspended over the outer surface;

a polymer dielectric layer surrounding a substantial portion of the inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, wherein the outer conductive sheath is not formed on the outer surface.

Claim 36 (previously presented): Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;

an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;

a polymer dielectric layer over a substantial portion of the inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, wherein the outer conductive sheath is not formed on the outer surface.

Claim 37 (previously presented): Integrated circuitry comprising:

- a substrate having an outer surface;
- a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;
- a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;
- a conductive layer of material disposed over and operably connected with the copper-comprising layer of material, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt and iron;
- a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding conductive layer portions which extend between the terminal members; and
- an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, wherein the outer conductive sheath is not formed on the outer surface.

Claim 38 (cancelled).

Claim 39 (cancelled).

Claim 40 (previously presented) The integrated circuitry of claim 35, wherein the polymer dielectric layer comprises parylene.

Claim 41 (previously presented) The integrated circuitry of claim 35, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

Claim 42 (previously presented) The integrated circuitry of claim 35, wherein the outer conductive sheath comprises aluminum.

Claim 43 (previously presented) The integrated circuitry of claim 35, wherein the inner conductive core comprises copper.

Claim 44 (previously presented) The integrated circuitry of claim 35, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

Claim 45 (currently amended) ~~he~~ The integrated circuitry of claim 36, wherein the polymer dielectric layer comprises parylene.

Claim 46 (previously presented) The integrated circuitry of claim 36, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

Claim 47 (previously presented) The integrated circuitry of claim 36, wherein the outer conductive sheath comprises aluminum.

Claim 48 (previously presented) The integrated circuitry of claim 36, wherein the inner conductive core comprises copper.

Claim 49 (previously presented) The integrated circuitry of claim 36, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

Claim 50 (previously presented) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the suspended inner conductive core; and  
an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed on the outer surface.

Claim 51 (previously presented) The integrated circuitry of claim 50, wherein the polymer dielectric layer comprises parylene.

Claim 52 (previously presented) The integrated circuitry of claim 50, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

Claim 53 (previously presented) The integrated circuitry of claim 50, wherein the outer conductive sheath comprises aluminum.

Claim 54 (previously presented) The integrated circuitry of claim 50, wherein the inner conductive core comprises copper.

Claim 55 (previously presented) The integrated circuitry of claim 50, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

Claim 56 (previously presented) Integrated circuitry comprising:

- a semiconductive substrate having an outer surface;
- a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;
- an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;
- a polymer dielectric layer surrounding the suspended inner conductive core; and
- an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer while some void space is present between the dielectric layer over the suspended inner conductive core and the outer surface, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface.

Claim 57 (previously presented) The integrated circuitry of claim 56, wherein the polymer dielectric layer comprises parylene.

Claim 58 (previously presented) The integrated circuitry of claim 56, wherein the polymer dielectric layer has a relative dielectric constant of about 2.6.

Claim 59 (previously presented) The integrated circuitry of claim 56, wherein the outer conductive sheath comprises aluminum.

Claim 60 (previously presented) The integrated circuitry of claim 56, wherein the inner conductive core comprises copper.

Claim 61 (previously presented) The integrated circuitry of claim 56, wherein the inner conductive core comprises a material chosen from a group consisting of nickel, cobalt and iron.

Claim 62 (previously presented) Integrated circuitry comprising:

a substrate having an outer surface;

a pair of upstanding, spaced-apart conductive terminal members disposed over the substrate outer surface;

a copper-comprising layer of material operably connected with and suspended above the outer surface between the terminal members, the copper-comprising layer having a thickness of between about 100 to 200 nanometers;

a conductive layer of material operably connected with the copper-comprising layer of material and suspended above the outer surface between the terminal members, the conductive layer comprising conductive material selected from the group consisting of copper, gold, nickel, cobalt, and iron;

a dielectric layer comprising parylene disposed over the conductive layer of material, the dielectric layer surrounding the suspended conductive layer portions; and

an outer conductive sheath of material disposed over the dielectric layer and surrounding dielectric layer portions which extend between the terminal members, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface.



Claim 63 (previously presented) The integrated circuitry of claim 62, wherein the copper-comprising layer and the conductive layer of material operably connected with the copper comprising layer together define an inner conductive core that includes at least two different conductive materials.

Claim 64 (cancelled).

Claim 65 (previously presented): The integrated circuitry of claim 62, wherein the outer conductive sheath comprises aluminum.

Please add new claims 66-67 as follows:

66 (New) Integrated circuitry comprising:

a semiconductive substrate having an outer surface;

a pair of spaced-apart terminal members disposed over the outer surface and extending elevationally away therefrom;

an inner conductive core operably connected with and suspended between the spaced-apart terminal members above the outer surface;

a polymer dielectric layer surrounding the suspended inner conductive core; and

an outer conductive sheath surrounding a substantial portion of the polymer dielectric layer while some void space is present between the dielectric layer over the suspended inner conductive core and the outer surface, the outer conductive sheath leaving some void space between the outer conductive sheath and the outer surface, wherein the outer conductive sheath is not formed over the substrate outer surface, wherein the void space is formed by removing masking material from elevationally below conductive material portions extending between the terminal members.

67. (New) Integrated circuitry comprising:  
a semiconductive substrate having an outer surface;  
an inner conductive core spaced from and suspended over the outer surface;  
a polymer dielectric layer surrounding a substantial portion of the inner conductive core; and  
an outer conductive sheath completely surrounding the polymer dielectric layer, wherein the outer conductive sheath is not formed on the outer surface.